

The listing of Claims will replace all prior versions, and listings, of claims in the application.

**Listing of Claims:**

1-9. (Canceled)

10. (Currently Amended) An integrated circuit device comprising:  
an integrated circuit substrate in which source/drain regions are formed;  
a first interlevel dielectric layer which is formed on the integrated circuit substrate;  
gate line patterns which are formed in the first interlevel dielectric layer;  
contact pads which are present between adjacent gate line patterns in the first interlevel dielectric layer and electrically connected to the source/drain regions;  
a second interlevel dielectric layer which is formed on the first interlevel dielectric layer, wherein contact holes, through which the contact pads are exposed, are formed in the second interlevel dielectric layer;  
first contact spacers which are formed along the side walls of the contact holes, the first contact spacers being formed of silicon oxide;  
second contact spacers which are formed of silicon nitride and formed on the first contact spacers; and  
contact plugs which are present in the contact holes between the second contact spacers,  
wherein the conductive contact contacts the contact pad, wherein the first spacer extends along the side wall to contact the contact pad and wherein the second spacer does not contact the contact pad.

11-30. (Canceled)

31. (New) An integrated circuit device comprising:  
an integrated circuit substrate in which source/drain regions are formed;  
a first interlevel dielectric layer which is formed on the integrated circuit substrate;  
gate line patterns which are formed in the first interlevel dielectric layer;

contact pads which are present between adjacent gate line patterns in the first interlevel dielectric layer and electrically connected to the source/drain regions;

a second interlevel dielectric layer which is formed on the first interlevel dielectric layer, wherein contact holes, through which the contact pads are exposed, are formed in the second interlevel dielectric layer;

first contact spacers having a first dielectric constant, the first contact spacers formed along side walls of the contact holes;

second contact spacers having a second dielectric constant, the second contact spacers formed on the first contact spacers; and

contact plugs which are present in the contact holes between the second contact spacers,

wherein the conductive contact contacts the contact pad, wherein the first spacer extends along the side wall to contact the contact pad and wherein the second spacer does not contact the contact pad.